WANSEMI
万代半导体

WP4606

Enhancement Mode N+P-Channel Power MOSFET

SOP8/N+PMOS/30V/±20V/1.7V/5.5A/15mΩ/

-30V/±20V/-1.8V/-4.2A/32mΩ

Rev0.5

30V N+P-Channel MOSFET

1.Features

- Advanced trench technology
- Super low gate charge
- High density cell design for ultra low Rdson

2.Applications

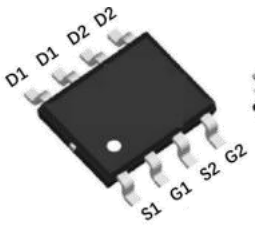
- DC/DC Converter
- PWM
- Load Switching

◆ N-Channel

V_{DS}	$R_{DS(on)}$ Typ.	I_D
30V	15mΩ @ 10V	5.5A
	22mΩ @ 4.5V	

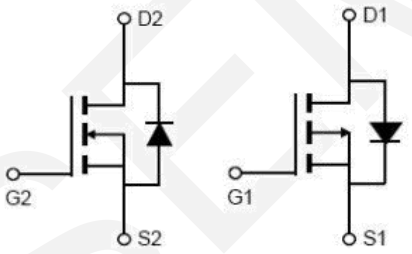
◆ P-Channel

V_{DS}	$R_{DS(on)}$ Typ.	I_D
-30V	32mΩ @ 10V	-4.2A
	46mΩ @ 4.5V	



SOP8

Pin Description



N-Channel P-Channel

Schematic Diagram

3.Package Marking and Ordering Information

Part no.	Marking	Package	PCS/Tube	PCS/CTN.
WP4606	4606	SOP8	4,000	48,000

4.Absolute Max Ratings at Ta=25℃ (Note1)

Parameter	Symbol	N-channel	P-channel	Units
Drain to Source Voltage	V_{DSS}	30	-30	V
Gate to Source Voltage	V_{GSS}	±20	±20	V
Drain Current (DC)	I_D	5.5	-4.2	A
Drain Current (Pulse), PW≤300μs	I_{DM}	30	-30	A
Total Dissipation	P_D	2.0	2.0	W
Avalanche Energy, Single Pulsed	EAS	30	25	mJ
Junction Temperature	T_j	150	150	℃
Storage Temperature	T_{stg}	-55 to +150	-55 to +150	℃

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of

these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

5.Thermal Resistance Ratings (Note 2)

Parameter	Symbol	Value	Unit
Maximum Junction-to-Ambient	$R_{\theta JA}$	63.2	℃/W

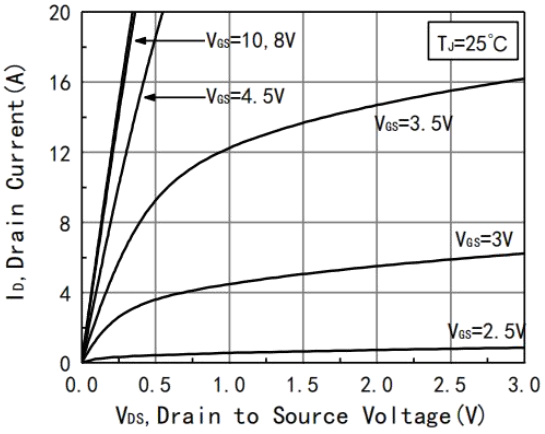
Note 2： When mounted on 1 inch square copper board t ≤ 10sec The value in any given application depends on the user's specific board design.

6.NMOS Electrical Characteristics at Ta=25℃ (Note 3)

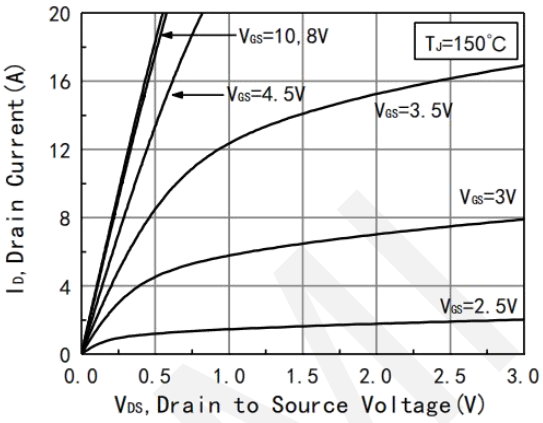
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	I_D = 250μA, V_{GS} = 0V	30	34		V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30V, V_{GS} = 0V			100	nA
Gate to Source Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_{DS}=250μA	1.1	1.7	2.5	V
Static Drain to Source On-State Resistance	$R_{DS(on)}$	I_D = 6A, V_{GS} = 10V		15	25	mΩ
		I_D = 6A, V_{GS} = 4.5V		22	39	mΩ
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=15V, Frequency=1.0MHz		457	-	pF
Output Capacitance	C_{oss}			74	-	pF
Reverse Transfer Capacitance	C_{rss}			63	-	pF
Turn-ON Delay Time	$t_{d(on)}$	V_{DD} = 15V, V_{GS} = 10V, R_{GEN} = 3Ω, I_D = 3A		10	-	ns
Rise Time	t_r			15	-	ns
Turn-OFF Delay Time	$t_{d(off)}$			30	-	ns
Fall Time	t_f			6	-	ns
Total Gate Charge	Q_g	V_{DS} =15V, V_{GS} = 10V, I_D = 1A		10		nC
	Q_{gs}			1		nC
	Q_{gd}			2.3		nC
Diode Forward Voltage	V_{FSD}	I_S = 6A, V_{GS} = 0V	0.5	0.8	1.1	V

Note 3： Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

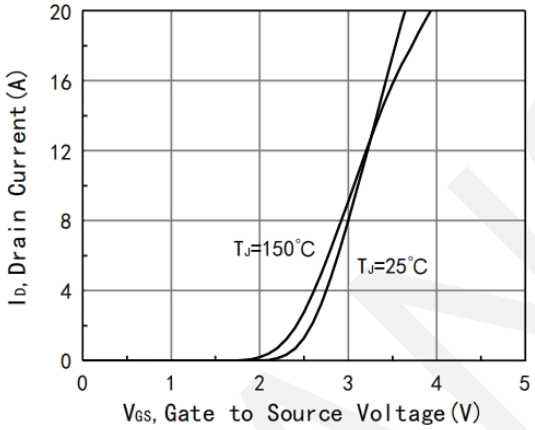
NMOS Typical electrical and thermal characteristics



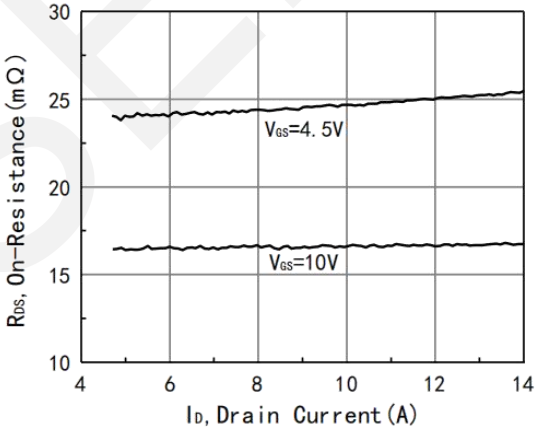
Typical Output Characteristics



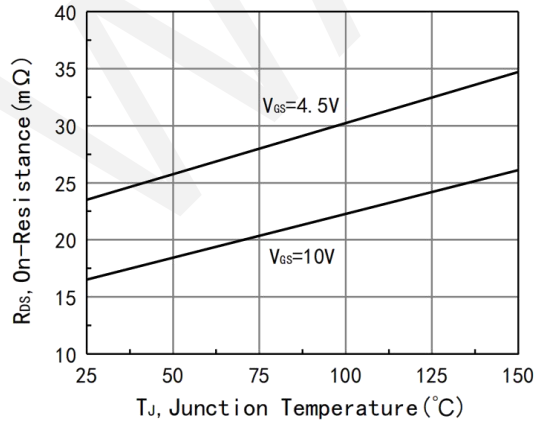
Typical Transfer Characteristics



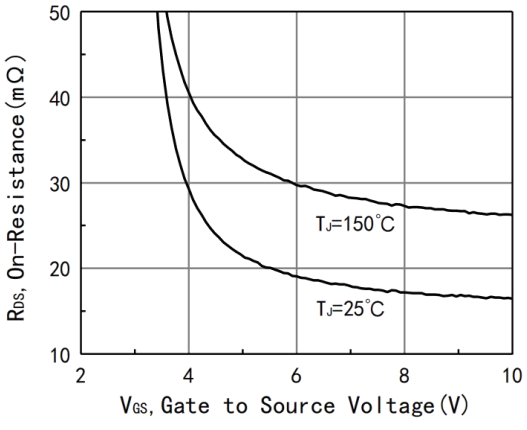
Typical Transfer Characteristics



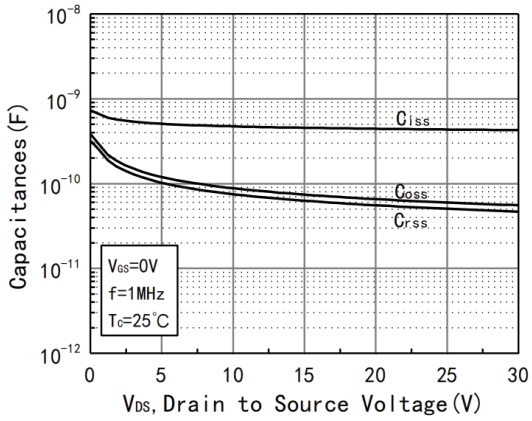
Rdson vs Id



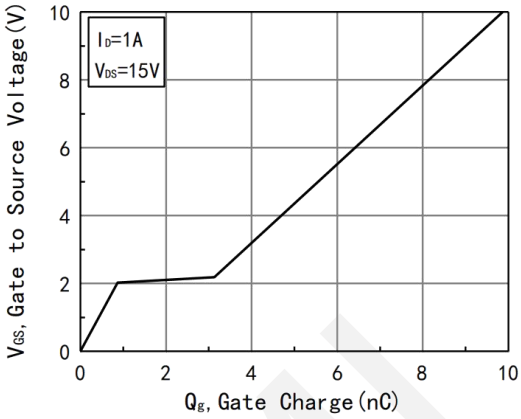
Rdson vs Tj



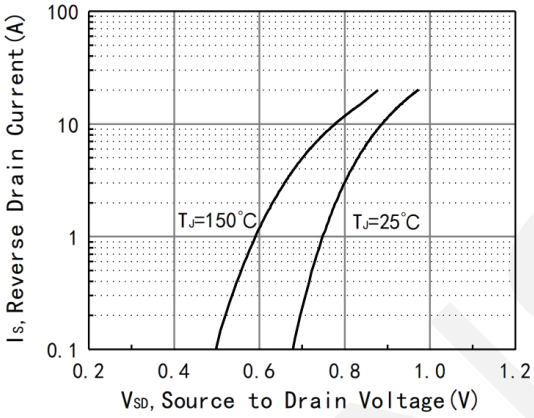
Rdson vs Vgs



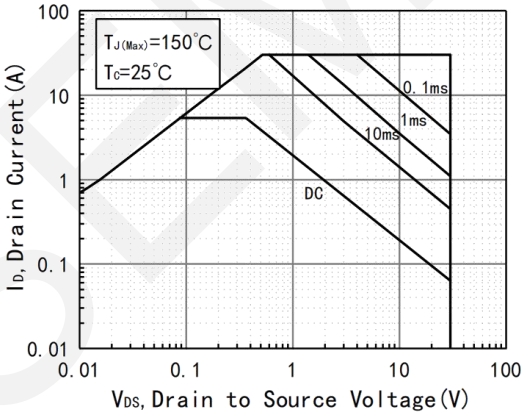
Capacitance vs Vds



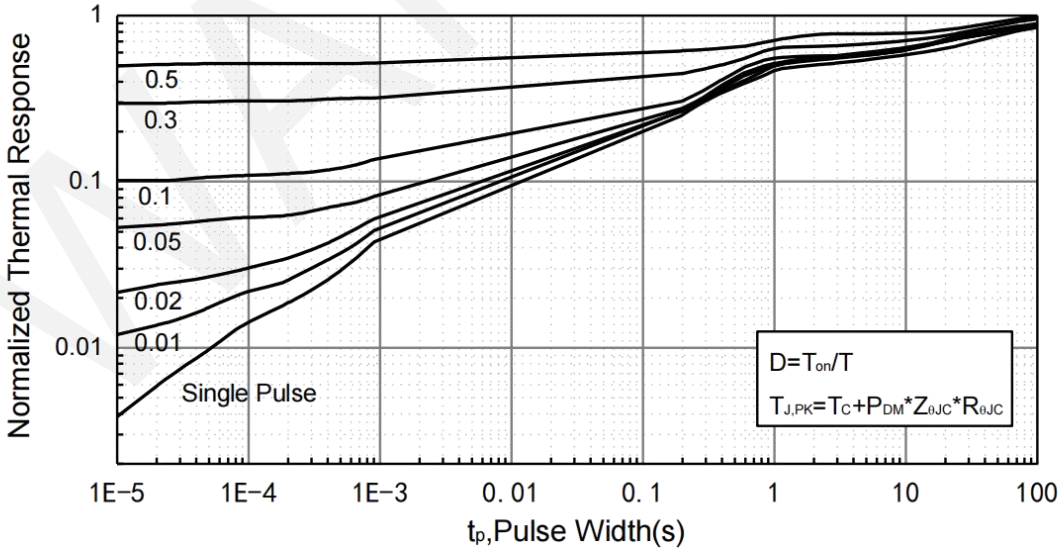
Gate Charge Characteristic



Diode Forward Characteristic



Safe Operating Area

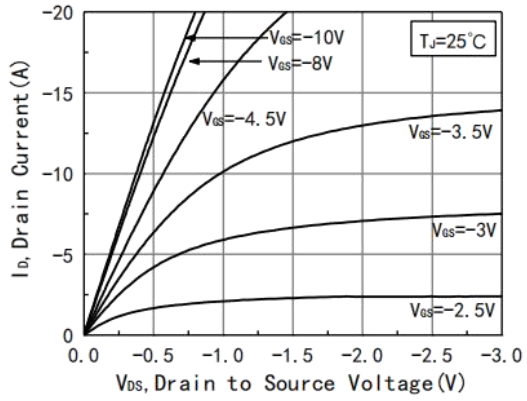


Normalized Maximum Transient Thermal Impedance

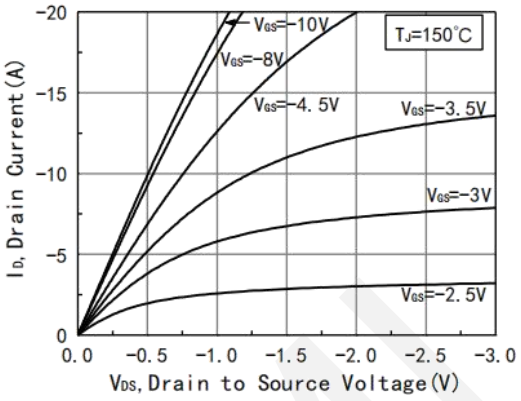
7.PMOS Electrical Characteristics at Ta=25℃

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	I_D = -250μA, V_{GS} = 0V	-30	-36		V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS} = -30V, V_{GS} = 0V			-100	nA
Gate to Source Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_{DS}=-250μA	-1.0	-1.8	-2.5	V
Static Drain to Source On-State Resistance	$R_{DS(on)}$	I_D = -5A, V_{GS} = -10V		32	39	mΩ
		I_D =-5A, V_{GS} =-4.5V		46	60	mΩ
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=-15V, Frequency=1.0MHz		550	-	pF
Output Capacitance	C_{oss}			85	-	pF
Reverse Transfer Capacitance	C_{rss}			75	-	pF
Turn-ON Delay Time	$t_{d(on)}$	V_{DD} = -15V, V_{GS} = -10V, R_{GEN} =3Ω, I_D = -3A		9.5	-	ns
Rise Time	t_r			5.5	-	ns
Turn-OFF Delay Time	$t_{d(off)}$			42.5	-	ns
Fall Time	t_f			13.6	-	ns
Total Gate Charge	Q_g	V_{DS} = -15V, V_{GS} = -10V, I_D = -1A		11		nC
	Q_{gs}			2.5		nC
	Q_{gd}			3		nC
Diode Forward Voltage	V_{FSD}	I_S = -5A, V_{GS} = 0V	-0.5	-0.9	-1.1	V

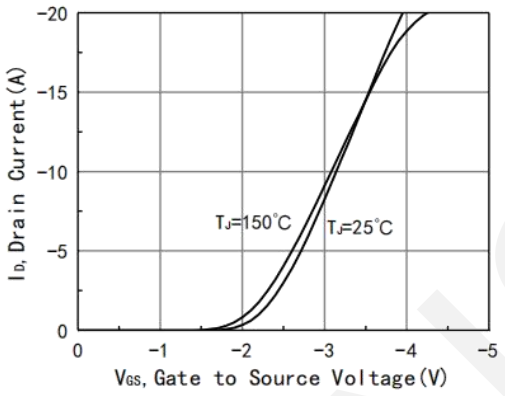
PMOS Typical electrical and thermal characteristics



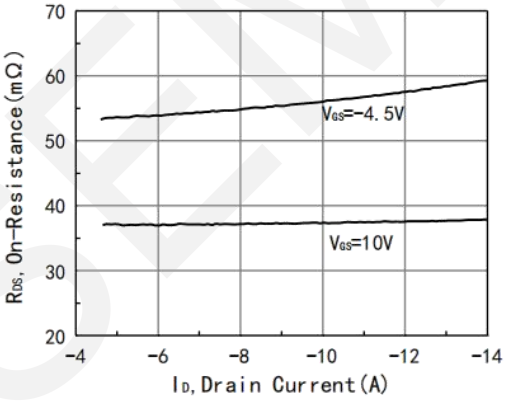
Typical Output Characteristics



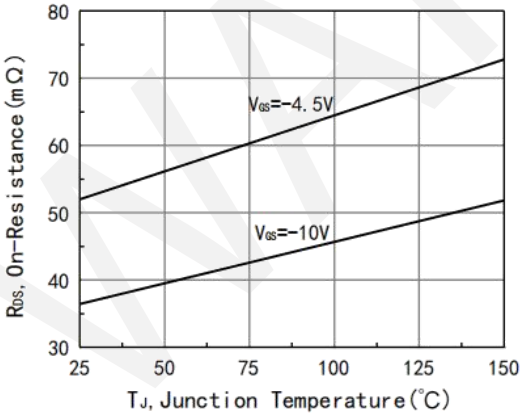
Typical Transfer Characteristics



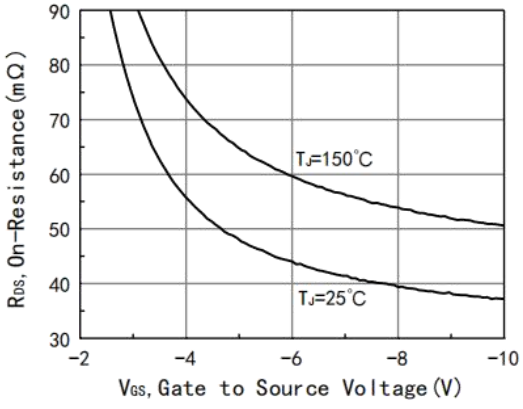
Typical Transfer Characteristics



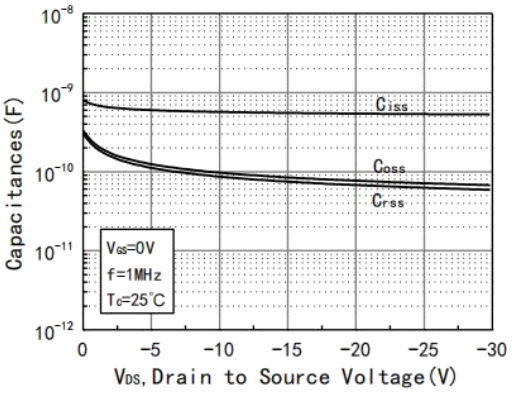
Rdson vs Id



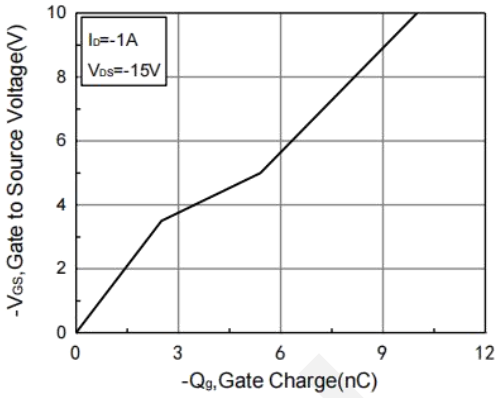
Rdson vs Tj



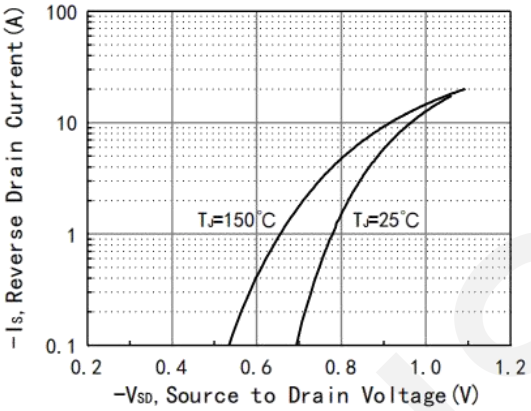
Rdson vs Vgs



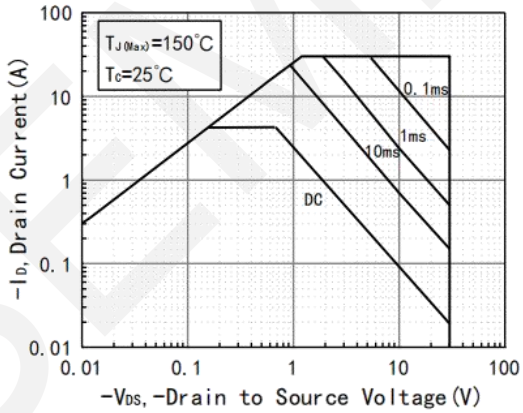
Capacitance vs Vds



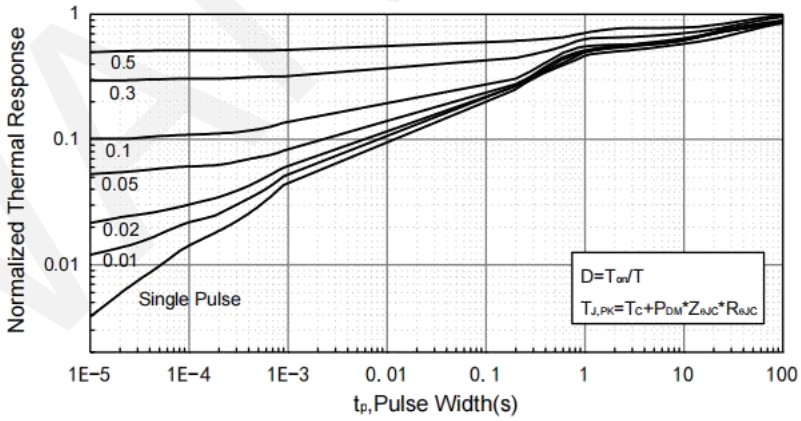
Gate Charge Characteristic



Diode Forward Characteristic

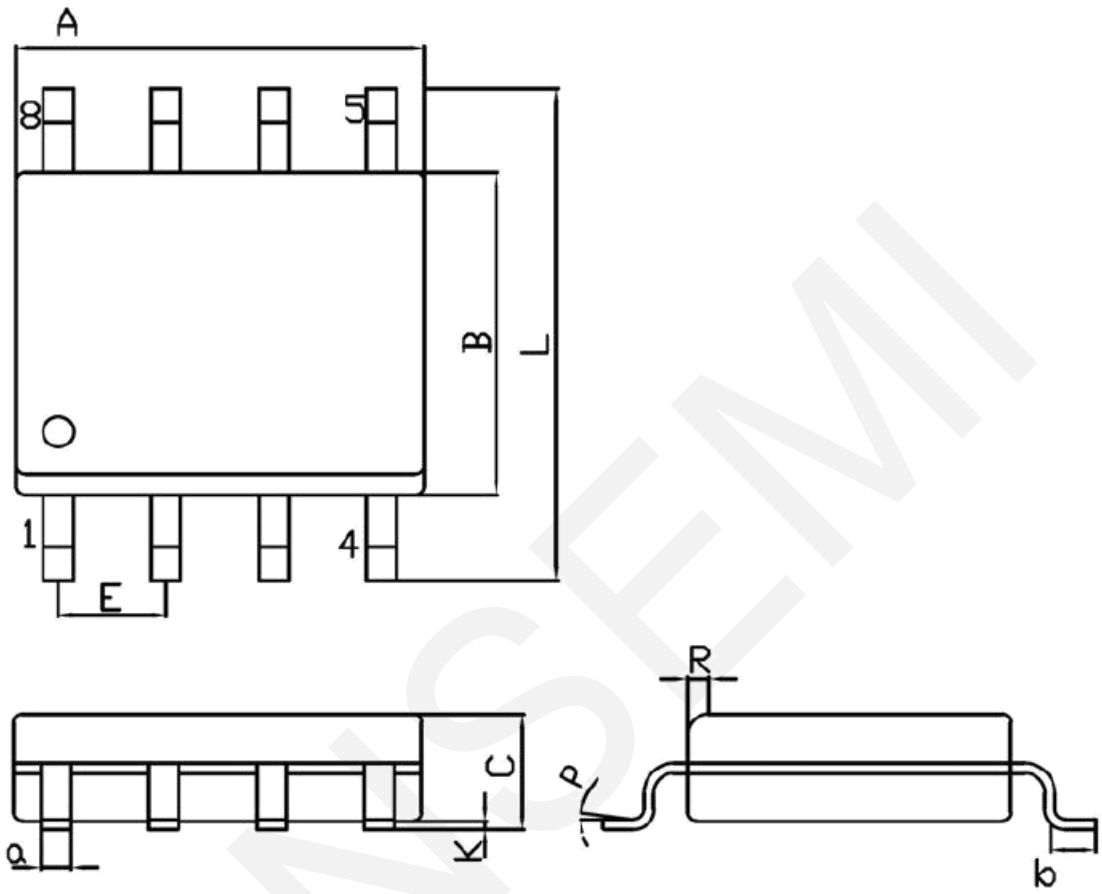


Safe Operating Area



Normalized Maximum Transient Thermal Impedance

8.Package Dimensions



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	4.70	5.10	C	1.35	1.75
B	3.70	4.10	a	0.35	0.49
L	5.80	6.20	R	0.30	0.60
E	1.27BSC		P	0°	7°
K	0.12	0.22	b	0.40	1.25

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